

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- Low Threshold
- High Input Impedance
- 110 pF Maximum Low-Input Capacitance
- Fast Switching Speeds
- Low On-Resistance
- Free from Secondary Breakdown
- Low Input and Output Leakage

Applications

- Logic-Level Interfaces (Ideal for TTL and CMOS)
- Solid-State Relays
- Battery-Operated Systems
- Photovoltaic Drives
- Analog Switches
- General Purpose Line Drivers
- Telecommunication Switches

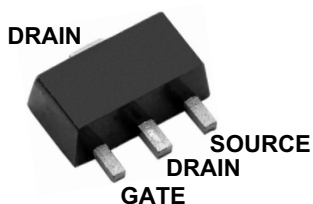
General Description

The TN2501 low-threshold Enhancement-mode (normally-off) transistor uses a vertical Diffusion Metal Oxide Semiconductor (DMOS) structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in Metal-Oxide Semiconductor (MOS) devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS Field-Effect Transistors (FETs) are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance and fast switching speeds are desired.

Package Type

3-lead SOT-89
(Top view)



See [Table 3-1](#) for pin information.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	$\pm 20V$
Operating Ambient Temperature, T_A	$-55^{\circ}C$ to $+150^{\circ}C$
Storage Temperature, T_S	$-55^{\circ}C$ to $+150^{\circ}C$

† **Notice:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: $T_A = 25^{\circ}C$ unless otherwise specified. All DC parameters are 100% tested at $25^{\circ}C$ unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle)

Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV_{DSS}	18	—	—	V	$V_{GS} = 0V, I_D = 1\text{ mA}$
Gate Threshold Voltage	$V_{GS(th)}$	0.3	—	1	V	$V_{GS} = V_{DS}, I_D = 1\text{ mA}$
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$	—	—	-4	mV/ $^{\circ}C$	$V_{GS} = V_{DS}, I_D = 1\text{ mA}$ (Note 1)
Gate Body Leakage Current	I_{GSS}	—	—	100	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
Zero-Gate Voltage Drain Current	I_{DSS}	—	—	10	μA	$V_{GS} = 0V,$ $V_{DS} = \text{Maximum rating}$
		—	—	1	mA	$V_{DS} = 0.8 \text{ Maximum rating},$ $V_{GS} = 0V, T_A = 125^{\circ}C$ (Note 1)
On-State Drain Current	$I_{D(ON)}$	250	600	—	mA	$V_{GS} = V_{DS} = 3V$
Static Drain-to-Source On-State Resistance	$R_{DS(ON)}$	—	—	25	Ω	$V_{GS} = 1.2V, I_D = 3\text{ mA}$
		—	—	3.5	Ω	$V_{GS} = 2V, I_D = 50\text{ mA}$
		—	—	2.5	Ω	$V_{GS} = 3V, I_D = 200\text{ mA}$
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	—	0.75	%/ $^{\circ}C$	$V_{GS} = 3V, I_D = 200\text{ mA}$ (Note 1)

Note 1: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T _A = 25°C unless otherwise specified. All AC parameters are sample tested.						
Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
Forward Transconductance	G _{FS}	150	300	—	mmho	V _{DS} = 3V, I _D = 200 mA
Input Capacitance	C _{ISS}	—	—	110	pF	V _{GS} = 0V, V _{DS} = 15V, f = 1 MHz
Common Source Output Capacitance	C _{OSS}	—	—	60	pF	
Reverse Transfer Capacitance	C _{RSS}	—	—	35	pF	
Turn-On Delay Time	t _{d(ON)}	—	—	5	ns	V _{DD} = 15V, I _D = 250 mA, R _{GEN} = 25Ω
Rise Time	t _r	—	—	15	ns	
Turn-Off Delay Time	t _{d(OFF)}	—	—	15	ns	
Fall Time	t _f	—	—	8	ns	
DIODE PARAMETER						
Diode Forward Voltage Drop	V _{SD}	—	1.1	1.8	V	V _{GS} = 0V, I _{SD} = 200 mA (Note 1)
Reverse Recovery Time	t _{rr}	—	100	—	ns	V _{GS} = 0V, I _{SD} = 200 mA

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated.
(Pulse test: 300 μs pulse, 2% duty cycle)

TEMPERATURE SPECIFICATIONS

Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
TEMPERATURE RANGE						
Operating Ambient Temperature	T_A	-55	—	+150	$^\circ\text{C}$	
Storage Temperature	T_S	-55	—	+150	$^\circ\text{C}$	
PACKAGE THERMAL RESISTANCE						
3-lead SOT-89	θ_{JA}	—	133	—	$^\circ\text{C/W}$	

THERMAL CHARACTERISTICS

Package	I_D (Note 1) (Continuous) (mA)	I_D (Pulsed) (mA)	Power Dissipation at $T_A = 25^\circ\text{C}$ (Note 2) (W)	I_{DR} (Note 1) (mA)	I_{DRM} (mA)
3-lead SOT-89	400	560	1.6	400	560

Note 1: I_D (continuous) is limited by maximum rated T_J .
2: $T_A = 25^\circ\text{C}$. Mounted on an FR4 Board, 25 mm x 25 mm x 1.57 mm.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

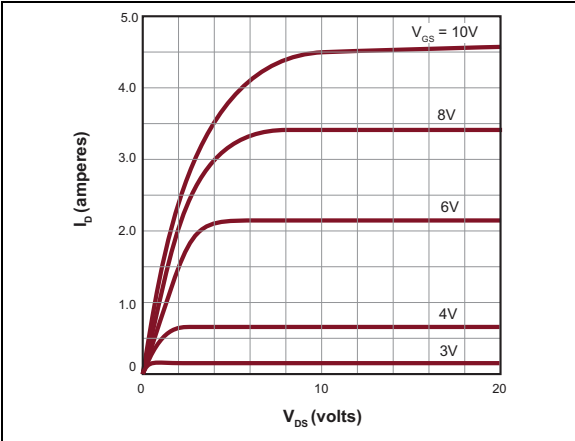


FIGURE 2-1: Output Characteristics.

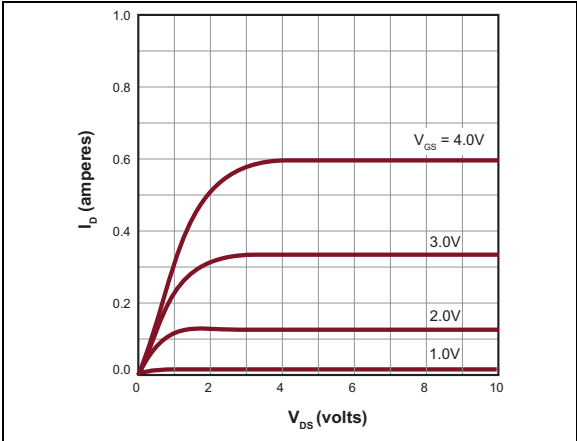


FIGURE 2-4: Saturation Characteristics.

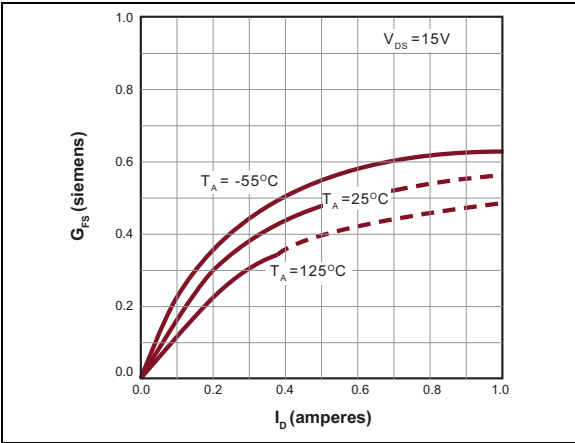


FIGURE 2-2: Transconductance vs. Drain Current.

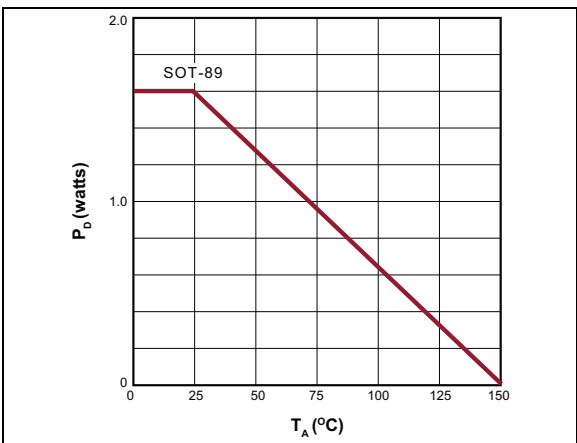


FIGURE 2-5: Power Dissipation vs. Ambient Temperature.

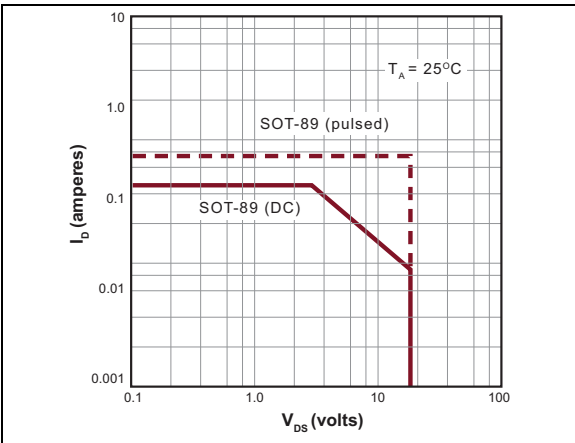


FIGURE 2-3: Maximum Rated Safe Operating Area.

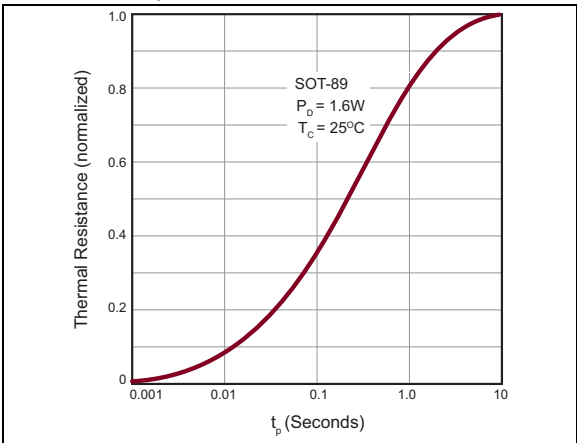


FIGURE 2-6: Thermal Response Characteristics.

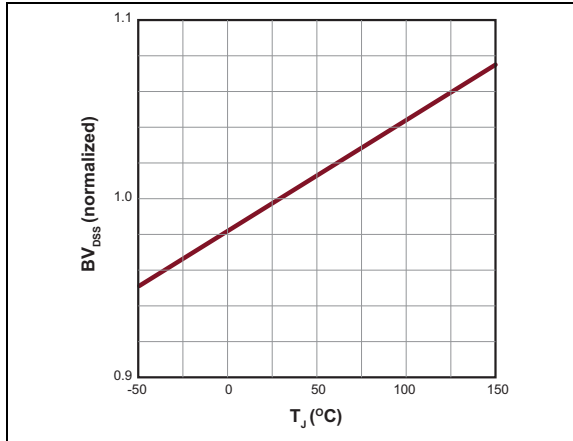


FIGURE 2-7: BV_{DSS} Variation with Temperature.

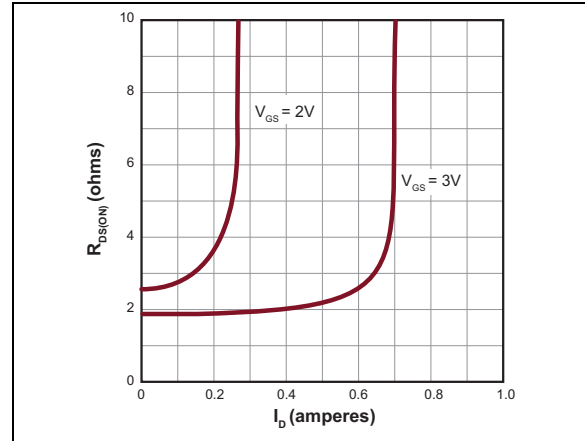


FIGURE 2-10: On-Resistance vs. Drain Current.

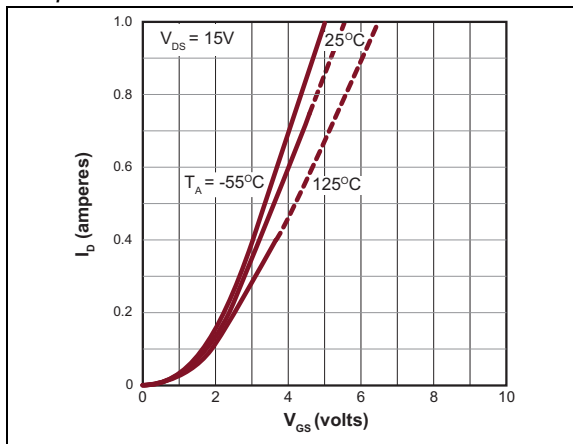


FIGURE 2-8: Transfer Characteristics.

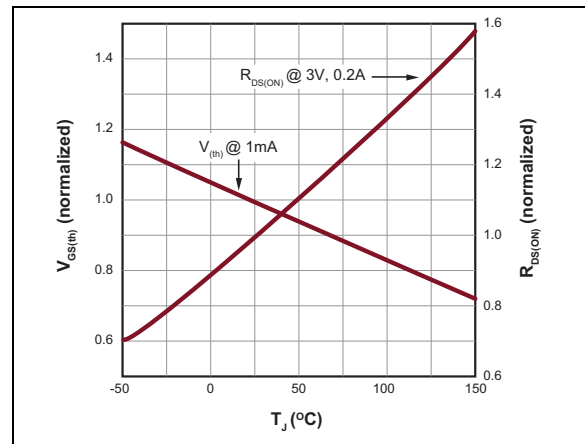


FIGURE 2-11: $V_{(th)}$ and R_{DS} Variation with Temperature.

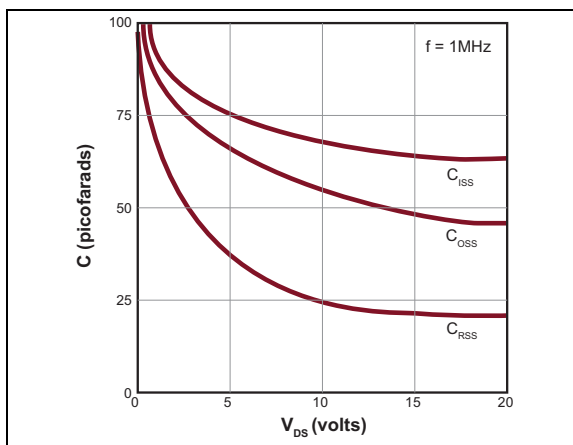


FIGURE 2-9: Capacitance vs. Drain-to-Source Voltage.

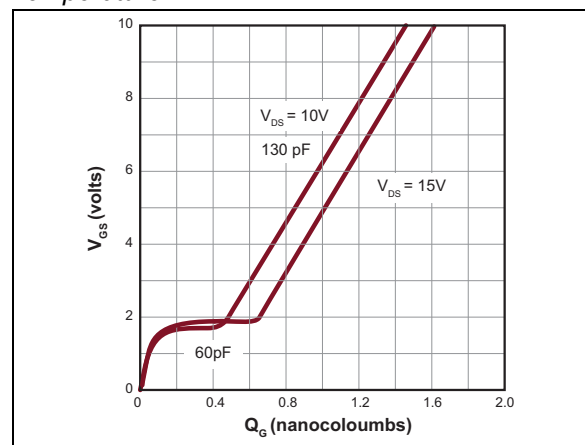


FIGURE 2-12: Gate Drive Dynamic Characteristics.

TN2501

3.0 PIN DESCRIPTION

The details on the pins of TN2501 are listed on [Table 3-1](#). Refer to [Package Type](#) for the location of pins.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Gate	Gate
2	Drain	Drain
3	Source	Source

4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TN2501.

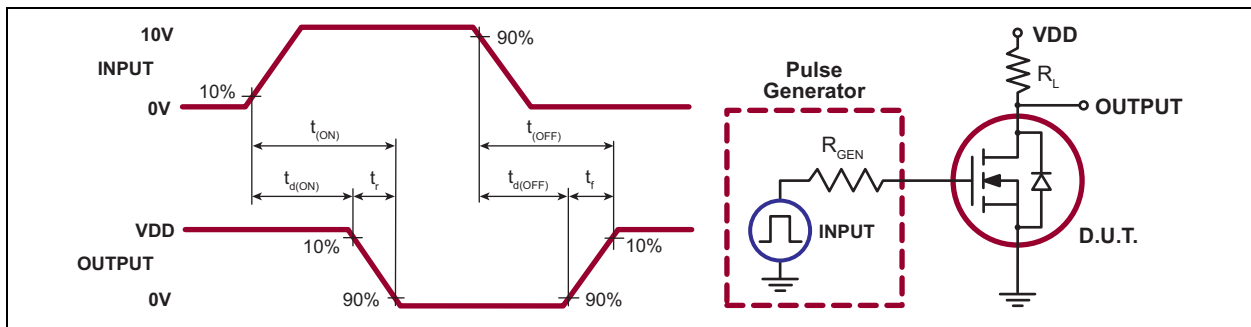


FIGURE 4-1: Switching Waveforms and Test Circuit.

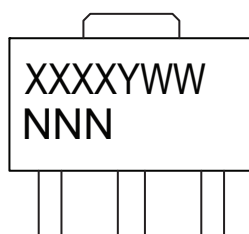
TABLE 4-1: PRODUCT SUMMARY

BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (Maximum) (Ω)	$I_{D(ON)}$ (Minimum) (mA)	$V_{GS(TH)}$ (Maximum) (V)
18	2.5	250	1

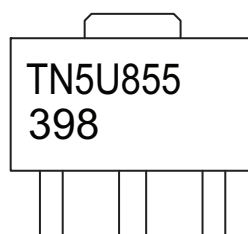
5.0 PACKAGING INFORMATION

5.1 Package Marking Information

3-lead SOT-89



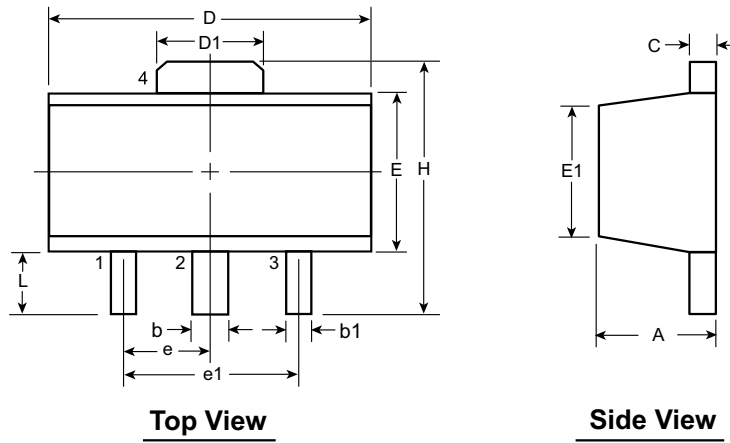
Example



Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

3-Lead TO-243AA (SOT-89) Package Outline (N8)



Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00 [†]	1.50 BSC	3.00 BSC	3.94	0.73 [†]
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

[†] This dimension differs from the JEDEC drawing

Drawings not to scale.

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (May 2018)

- Converted Supertex Doc# DSFP-TN2501 to Microchip DS20005948A
- Changed the package marking format
- Added some sections to comply with Microchip formatting standards
- Made minor text changes throughout the document

TN2501

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

<u>PART NO.</u>	<u>XX</u>	-	<u>X</u>	-	<u>X</u>
Device	Package Options		Environmental		Media Type
Device:	TN2501	=	N-Channel Enhancement-Mode Vertical DMOS FET		
Package:	N8	=	3-lead SOT-89		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	2000/Reel for an N8 Package		

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